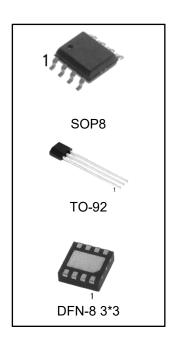


#### **Description**

The LM236 and LM336 are precision 2.5V regulator diodes. These voltage reference monolithic ICs operate like 2.5V zener diodes with a low temperature coefficient and a dynamic impedance of 0.2  $\Omega$ . A third pin enables adjusting the reference voltage and the temperature coefficient.

#### **Features**

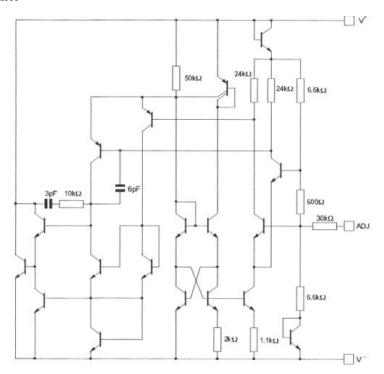
- Low temperature coefficient
- Wide operating current of 400μA to 10 mA
- 0.2Ω dynamic impedance
- ± 1% initial tolerance available
- Guaranteed temperature stability
- Fast turn-on



#### **Ordering Information**

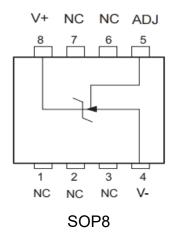
DEVICE	Package Type	MARKING	Packing	Packing Qty
LM236M-2.5/TR	SOP8	236-2.5	Reel	2500pcs/reel
LM336M-2.5/TR	SOP8	336-2.5	Reel	2500pcs/reel
LM236Z-2.5	TO-92	LM236-2.5	Tape	1000pcs/box
LM336Z-2.5	TO-92	LM336-2.5	Таре	1000pcs/box
LM236DQ-2.5/TR	DFN-8 3*3	236-2.5	Reel	2500pcs/reel
LM336DQ-2.5/TR	DFN-8 3*3	336-2.5	Reel	2500pcs/reel

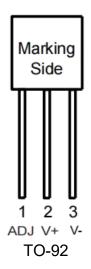
#### **Schematic Diagram**

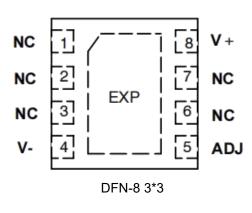




#### **Pin Connections**







## **Absolute Maximum Ratings**

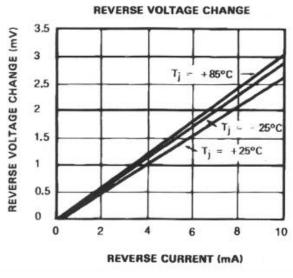
Symbol	Parameter	LM336	Unit
	Current		
IRIF	Reverse	15	mA
	Forward	10	
Toper	Operating Free-air Temperature Range	LM336-2.5: 0 to +70	°C
	Operating Free-all Temperature Mange	LM236-2.5: -40 to +85	°C
T <sub>Stg</sub>	Storage Temperature Range	-65 to +150	°C

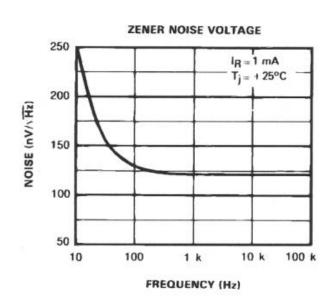
## **Electrical Characteristics**

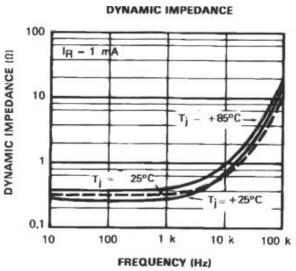
Council of	Danamatan	LM	11:4		
Symbol	Parameter	Min.	Тур.	Max.	Unit
	Reference Breakdown Voltage				
VR	$T_{amb}$ = +25°C, $I_R$ = 1mA	2.44	2.49	2.54	V
	LM336				
	Reverse Breakdown Voltage Change with Current				
ΔVR	$400\mu$ A $\leq$ I <sub>R</sub> $\leq$ 10mA				
ΔVR	$T_{amb} = +25$ °C	_	2.6	10	mV
	$T_{min.} \le T_{amb} \le T_{max.}$		3	12	
	Reverse Dynamic Impedance (I <sub>R</sub> = 1mA)				
Z <sub>D</sub>	$T_{amb} = +25^{\circ}C$	-	0.2	1	Ω
	$T_{min.} \le T_{amb} \le T_{max.}$		0.4	1.4	
KVT	Temperature Stability ( $V_R = 2.49V$ , $I_R = 1mA$ )	-	1.8	6	mV
K <sub>VH</sub>	Long Term Stability (T <sub>amb</sub> = +25°C ±0.1°C, I <sub>R</sub> = 1mA)	-	20	-	ppm

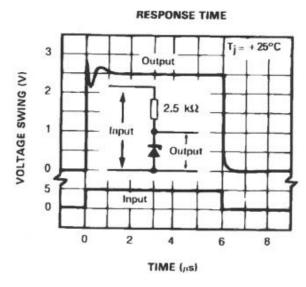


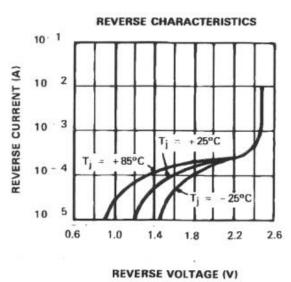
## **Typical Performance Characteristics**

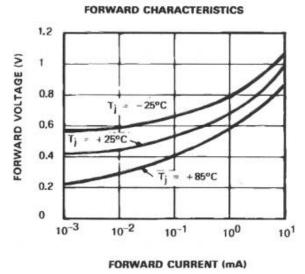






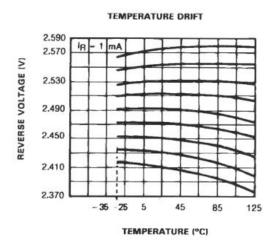








#### **Typical Performance Characteristics** (Continued)



#### **Application Hints**

The LM336 voltage references are easier to use than zener diodes. Their low impedance and wide current range facilitate biasing in any circuits. Besides, the breakdown voltage or the temperature coefficient can be adjusted so as to optimize the performance of the circuit.

Figure 1 represents a LM336 with a  $10k\Omega$  potentiometer to adjust the reverse breakdown voltage which can be adjusted without altering the temperature coefficient of the circuit. The adjustment range is generally sufficient to adjust the initial tolerance of the circuit and the inaccuracy of the amplifier circuit.

To obtain a lower temperature coefficient two diodes can be connected in series as indicated in Figure 2.

When the circuit is adjusted to 2.49V the temperature coefficient is minimized. For a correct temperature coefficient, the diodes should be at the same ambient temperature as the LM336. The value of R1 is not critical (2-20k $\Omega$ ).

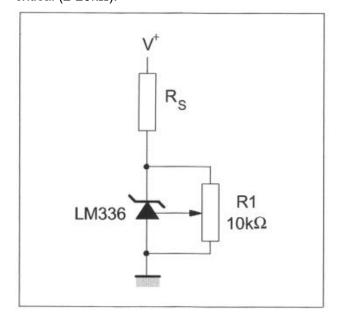


FIGURE1.LM336 with Pot for Adjustment of Breakdown Voltage

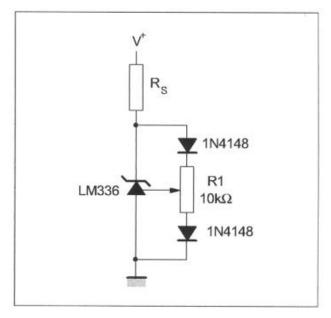


FIGURE 2. Temperature Coefficient Adjustment



### **Typical Applications**

Figure 3:2.5V Reference

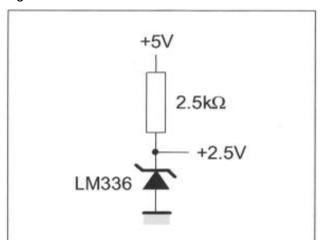


Figure 4: Wide Input Range Reference

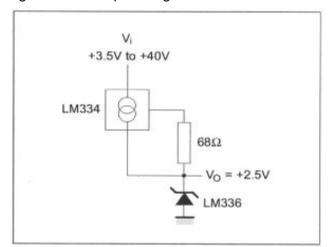


Figure 5 : Precision Power Regulator with Low Temperature Coefficient

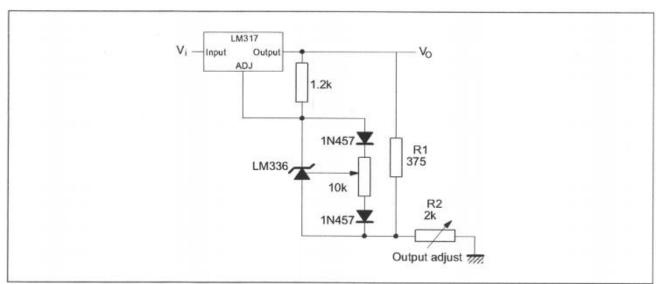


Figure 5 :Adjustable Shunt Regulator

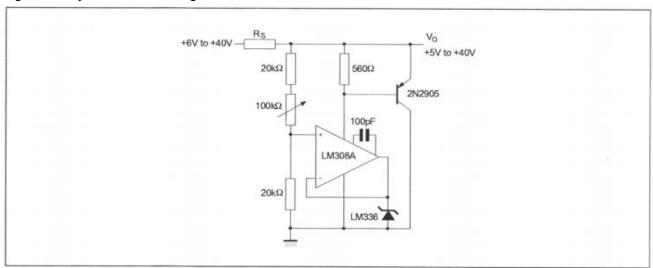




Figure 7 :Linear Ohmmeter

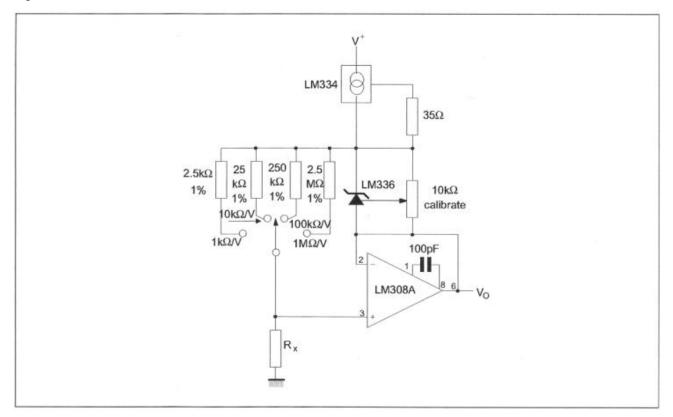


Figure 8 :Bipolar Output Reference

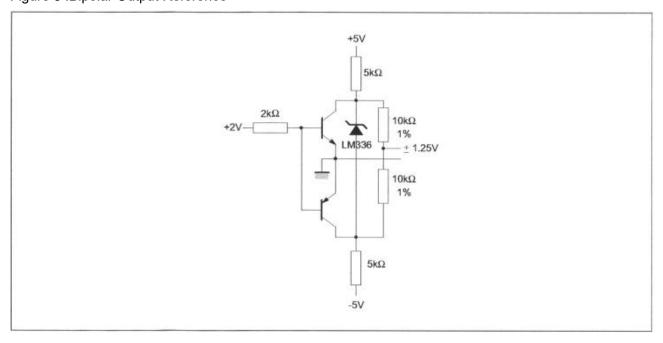




Figure 9:5V Buffered Reference

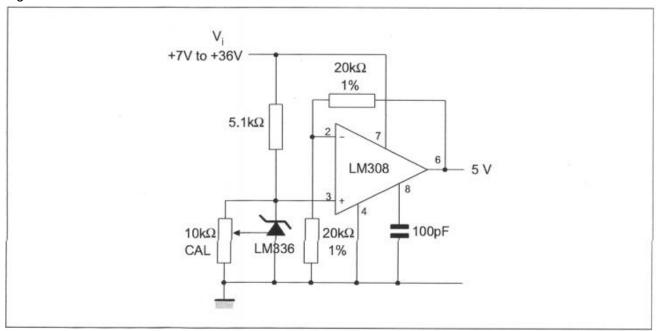
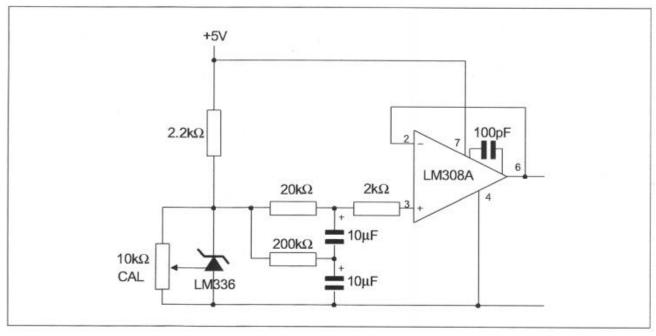


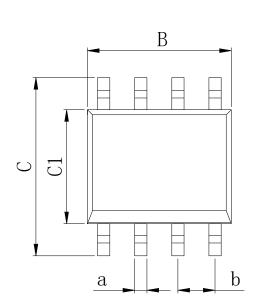
Figure 10 : Low Noise Buffered Reference

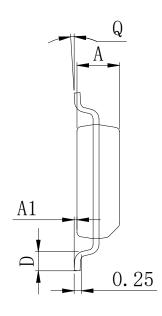




## **Physical Dimensions**

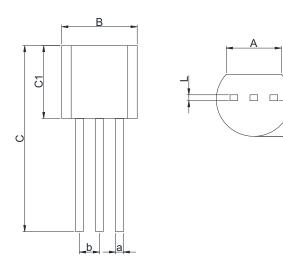
## SOP8





Dimensions In Millimeters(SOP8)										
Symbol:	Α	A1	В	С	C1	D	Q	а	b	
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC	
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	1.27 650	

TO-92

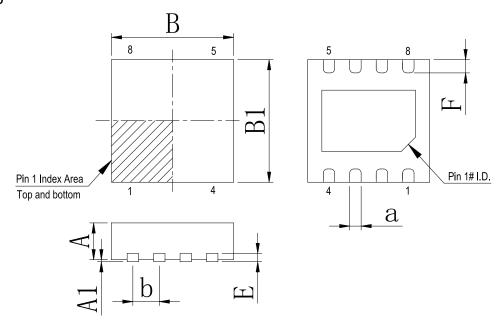


Dimensions In Millimeters(TO-92)										
Symbol:	Α	В	С	C1	D	D1	L	а	b	
Min:	3.43	4.44	11.2	4.32	3.17	2.03	0.33	0.40	1.27BSC	
Max:	3.83	5.21	12.7	5.34	4.19	2.67	0.42	0.52	1.27650	



# **Physical Dimensions**

## DFN-8 3\*3



Dimensions In Millimeters(DFN-8 3*3)										
Symbol:	А	A1	В	B1	Е	F	а	b		
Min:	0.85	0.00	2.90	2.90	0.20	0.30	0.20	0.65 BSC		
Max:	0.95	0.05	3.10	3.10	0.25	0.50	0.34	0.65 BSC		



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